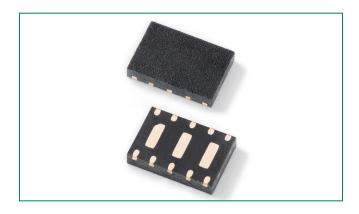


SP2555NUTG 2.5V 45A Diode Array



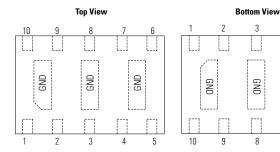


Description

The SP2555NUTG is a low-capacitance, TVS Diode Array designed to provide protection against ESD (electrostatic discharge), CDE (cable discharge events), EFT (electrical fast transients), and lightning induced surges for high-speed, differential data lines. It's packaged in a μ DFN package (3.0 x 2.0mm) and each component can protect up 4 channels or 2 differential pairs, up to 45A (IEC 61000-4-5 2nd edition,) and up to 30kV ESD (IEC 61000-4-2). The "flow-through" design minimizes signal distortion, reduces voltage overshoot, and provides a simplified PCB design.

The SP2555NUTG with its low capacitance and low clamping voltage makes it ideal for high-speed data interfaces such as 1GbE applications found in notebooks, switches, etc.

Pinout



NOTE: PIN3, PIN8 are same potential with GND

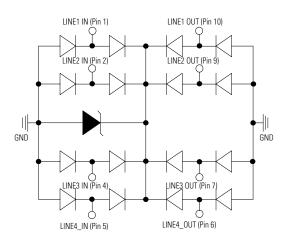
Features

GND

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 45A (8/20µs as defined in IEC 61000-4-5 2nd Edition)
- Low capacitance of 2.5pF@0V (TYP) per I/O
- Low leakage current of 0.1µA (TYP) at 2.5V

- µDFN-10 package is optimized for high-speed data line routing
- Provides protection for two differential data pairs (4 channels) up to 45A
- Low operating and clamping voltage
- AEC-Q101 qualified
- Halogen free, Lead free and RoHS compliant

Functional Block Diagram



Life Support Note:

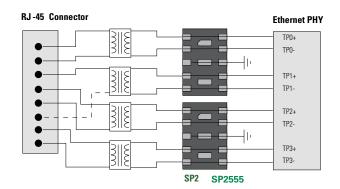
Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Applications

- •10/100/1000 Ethernet
- WAN/LAN Equipment
- Desktops, Servers and Notebooks
- LVDS Interfaces
- Integrated Magnetics
- Smart TV

Application Example



TVS Diode Array (SPA®Diodes) Lightnign Surge Protection - SP2555NUTG

Absolute Maximum Ratings

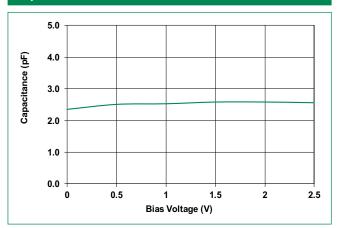
Symbol	Parameter	Value	Units
l _{pp}	Peak Current (t _p =8/20µs)	45	А
P _{Pk}	Peak Pulse Power (t _p =8/20µs)	1000	W
T _{OP}	Operating Temperature	-40 to 125	°C
T _{STOR}	Storage Temperature	-55 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

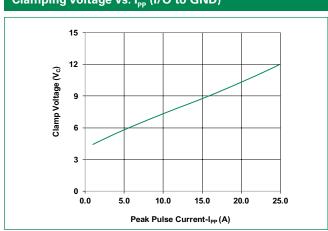
Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V _{RWM}	$I_R \le 1 \mu A$			2.5	V
Reverse Leakage Current	I _R	V _{RWM} = 2.5V, T = 25°C		0.1	0.5	μA
Snap Back Voltage	V _{SB}	I _{SB} = 50mA	2.0			V
Clamp Voltage	V _c	$I_{pp} = 1A$, $t_p = 8/20 \mu s$, Any I/O to Ground		4.5		V
		$I_{pp} = 10A$, $t_p = 8/20\mu s$, Any I/O to Ground		7.5		
		$I_{pp} = 25A$, $t_p = 8/20\mu s$, Any I/O to Ground		12		
		l _{pp} = 45A, t _p = 8/20μs, Line-to-Line ¹ , two I/O Pins connected together on each line		19		
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Any I/O to Ground		0.1		Ω
ESD Withstand Voltage	V _{ESD}	IEC 61000-4-2 (Contact)	±30			kV
		IEC 61000-4-2 (Air)	±30			kV
Diode Capacitance	C _{I/O to GND}	Between I/O Pins and Ground V_ = 0V. f = 1MHz		2.5		pF
•	C _{I/O to I/O}	V _{o.} = 0V, f = 1MHz Between I/O Pins V _{o.} = 0V, f = 1MHz		1.2		pF

Capacitance vs. Reverse Bias

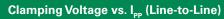


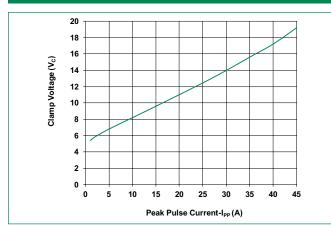
Clamping Voltage vs. I_{pp} (I/O to GND)



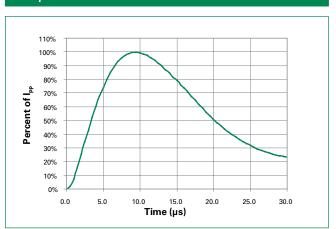
Rating with 2 pins connected together per sugguested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6)
 Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2=90ns



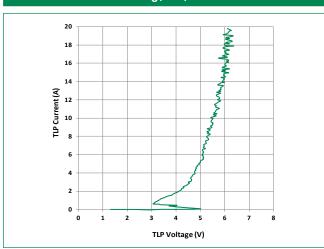




8/20µs Pulse Waveform



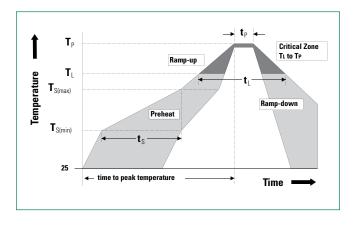
Transmission Line Pulsing(TLP) Plot





Soldering Parameters

Reflow Condition		Pb – Free assembly	
Pre Heat	- Temperature Min (T _{s(min)})	150°C	
	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 180 secs	
Average ramp up rate (Liquidus) Temp (T _L) to peak		3°C/second max	
T _{S(max)} to T _L - Ramp-up Rate		3°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
	-Temperature (t _L)	60 – 150 seconds	
Peak Temperature (T _P)		260+0/-5 °C	
Time within 5°C of actual peak Temperature (tp)		20 - 40 seconds	
Ramp-down Rate		6°C/second max	
Time 25°C to peak Temperature (T _P)		8 minutes Max.	
Do not exceed		260°C	



Ordering Information

Part Number	Package	Min. Order Qty.
SP2555NUTG	μDFN-10 (3.0x2.0mm)	3000

Part Numbering System

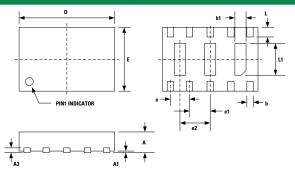
TVS Diode Arrays (SPA® Diodes) Series T= Tape & Reel Package µDFN-10 (3.0x2.0mm)

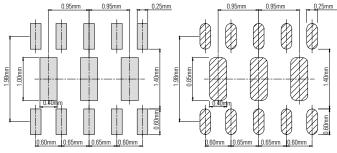
Part Marking System





Package Dimensions - µDFN-10 (3.0x2.0mm)





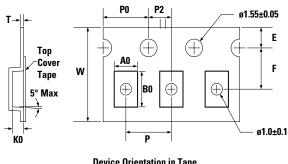
Recommended Stencil Apertures Recommended Stencil thickness 5mils

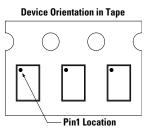
Package μDFN-10 (3.0x2.0mm) JEDEC MO-229 Millimeters Inches **Symbol** Nom Max Min Nom Α 0.50 0.60 0.65 0.020 0.024 0.026 Α1 0.00 0.03 0.05 0.000 0.001 0.002 А3 0.15 Ref 0.006 Ref 0.25 b 0.15 0.20 0.006 0.008 0.010 0.018 h1 0.25 0.35 0.45 0.010 0.014 0.114 D 2.90 3.00 3.10 0.118 0.122 0.075 Ε 1.90 2.00 2.10 0.079 0.083 е 0.60 BSC 0.024 BSC е1 0.65 BSC 0.026 BSC e2 0.95 BSC 0.037 0.25 0.30 0.35 0.010 0.012 0.014 L1 0.95 1.05 0.037 0.039 0.041 1.00

- All dimensions are in millimeters
- Dimensions include solder plating.
 Dimensions are exclusive of mold flash & metal burr

Tape & Reel Specification - µDFN-10 (3.0x2.0mm)

Recommended Soldering Pads Layout





Package	μDFN-10 (3.0x2.0mm)	
Symbol	Millimeters	
Α0	2.30 +/- 0.10	
В0	3.20 +/- 0.10	
E	1.75 +/- 0.10	
F	3.50 +/- 0.05	
КО	1.0 +/- 0.10	
P	4.00 +/- 0.10	
P0	4.00 +/- 0.10	
P2	2.00 +/- 0.10	
Т	0.3 +/- 0.05	
W	8.00 +0.30/- 0.10	